## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60610NY

### 2. Features and benefits

- · High thermal power dissipation capability
- High temperature applications up to 175 °C
- · Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-60	V
I <sub>C</sub>	collector current		-	-	-10	Α
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms	-	-	-20	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -10 A; $I_B$ = -1 A; $t_p$ ≤ 300 μs; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	29	47	mΩ



60 V, 10 A PNP high power bipolar transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		B—
3	Е	emitter	a	, h
4	В	base	0.000	É sym132
mb	С	collector	1 2 3 4	·
			LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number Package						
	Name	Description	Version			
PHPT60610PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PHPT60610PY	0610PAB

60 V, 10 A PNP high power bipolar transistor

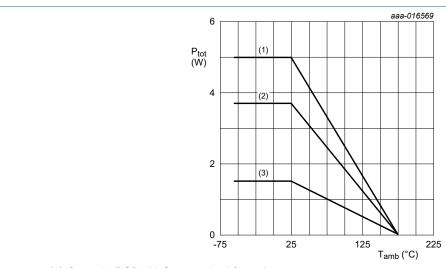
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
Ic	collector current			-	-10	А
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-20	А
I <sub>B</sub>	base current			-	-1.5	Α
I <sub>BM</sub>	peak base current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

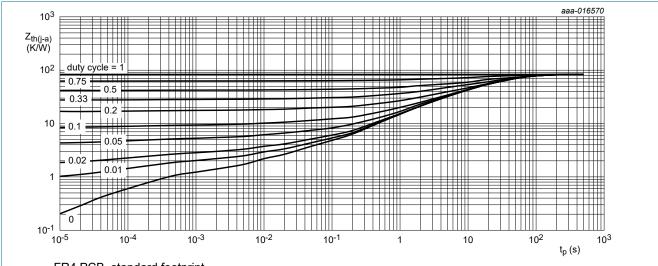
#### 60 V, 10 A PNP high power bipolar transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

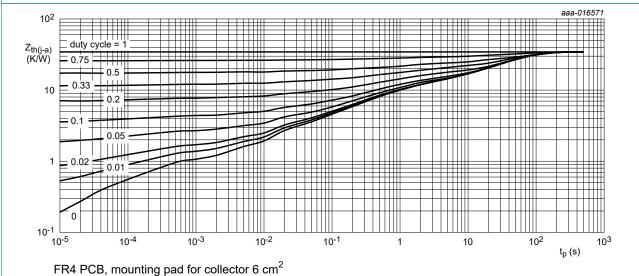
A	B	0			-		11.14
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
111(J-a)	thermal resistance from	[1] [2] [3]	[1]	-	-	100	K/W
	junction to ambient		[2]	-	-	41	K/W
			[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 3.

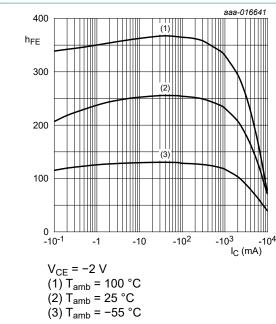
### 60 V, 10 A PNP high power bipolar transistor

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	120	215	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	120	205	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -5 A; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	70	130	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -10 A; $t_{p}$ ≤ 300 μs; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	30	55	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-50	-80	mV
		$I_C$ = -5 A; $I_B$ = -500 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C; pulsed	-	-130	-220	mV
		$I_C = -10 \text{ A}; I_B = -1 \text{ A}; t_p \le 300 \text{ µs};$	-	-290	-470	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	pulsed; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	29	47	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; $t_p$ ≤ 300 μs; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-0.95	V
		$I_C$ = -5 A; $I_B$ = -500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.1	V
		$I_C$ = -10 A; $I_B$ = -1 A; $t_p \le 300 \mu s$ ; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.3	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V; } I_{C} = -500 \text{ mA; } T_{amb} = 25 \text{ °C}$	-	-	-0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -5 A; I <sub>Bon</sub> = -250 mA;	-	25	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 250 mA; T <sub>amb</sub> = 25 °C	-	105	-	ns
t <sub>on</sub>	turn-on time		-	130	-	ns
t <sub>s</sub>	storage time		-	165	-	ns
t <sub>f</sub>	fall time		-	55	-	ns
t <sub>off</sub>	turn-off time		-	220	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	85	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	135	-	pF

#### 60 V, 10 A PNP high power bipolar transistor



$$V_{CE} = -2 V$$
(1) T . = 100 °C

$$(3) T_{amb} = -55 ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values

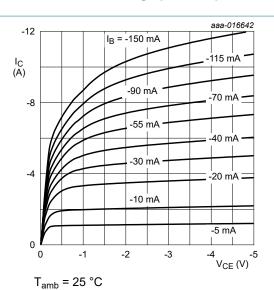
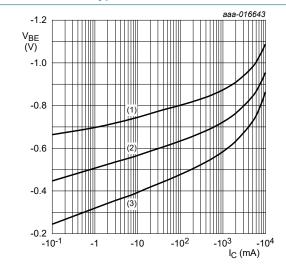


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



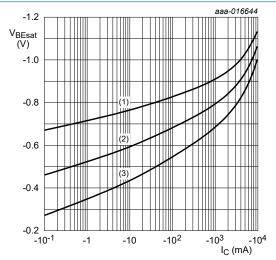
$$V_{CE} = -2 V$$

$$(1) T_{amb} = -55 °C$$

$$(2) T_{amb} = 25 °C$$

(3) T<sub>amb</sub> = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

#### 60 V, 10 A PNP high power bipolar transistor

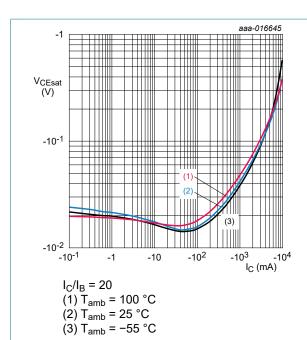


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

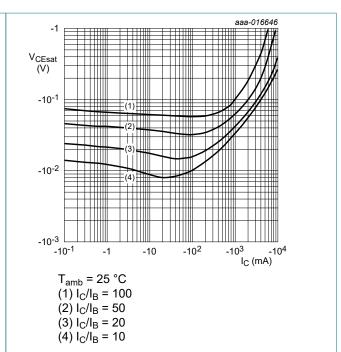
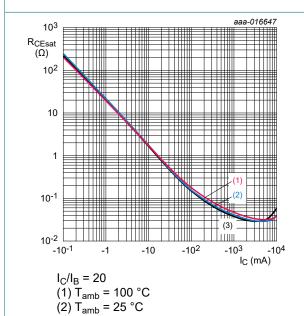
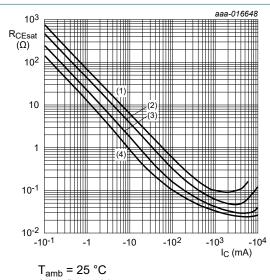


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



(3) T<sub>amb</sub> = −55 °C Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

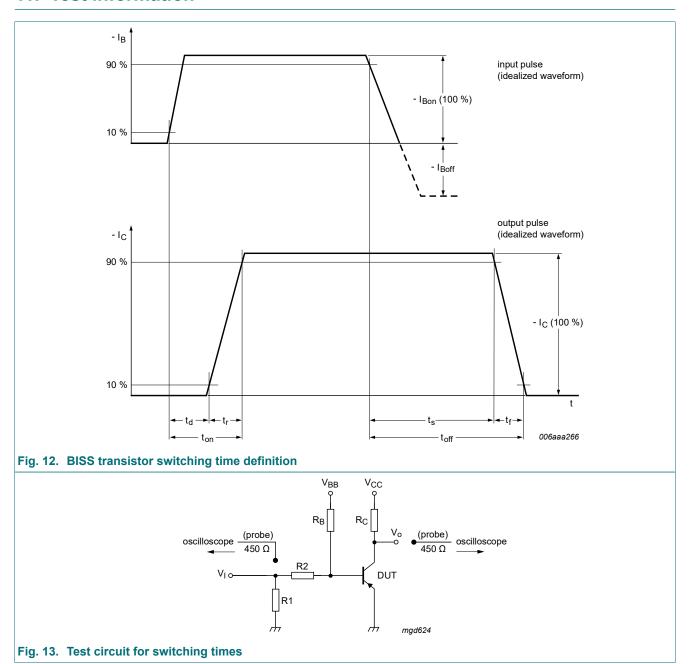


(1)  $I_C/I_B = 100$ (2)  $I_C/I_B = 50$ (3)  $I_C/I_B = 20$ (4)  $I_C/I_B = 10$ 

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 10 A PNP high power bipolar transistor

### 11. Test information



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 10 A PNP high power bipolar transistor

# 12. Package outline

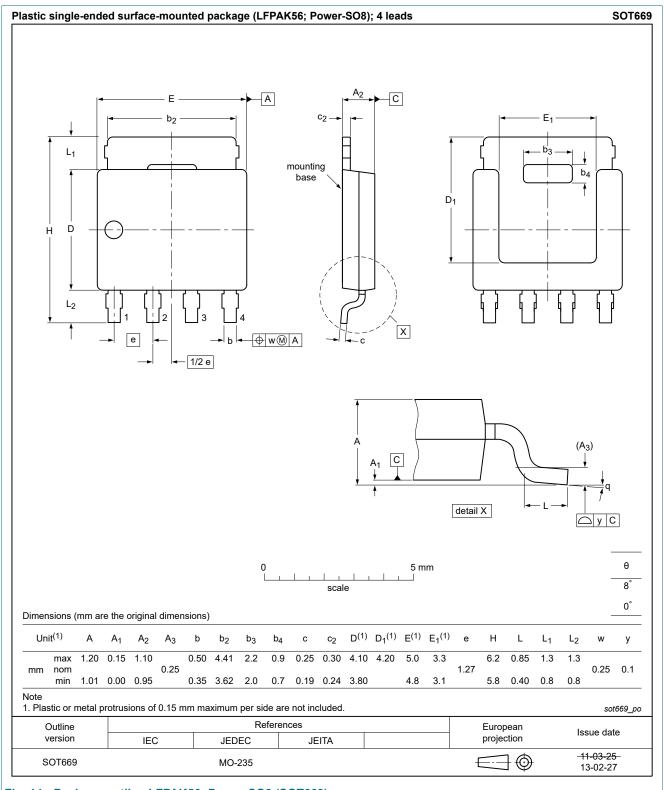
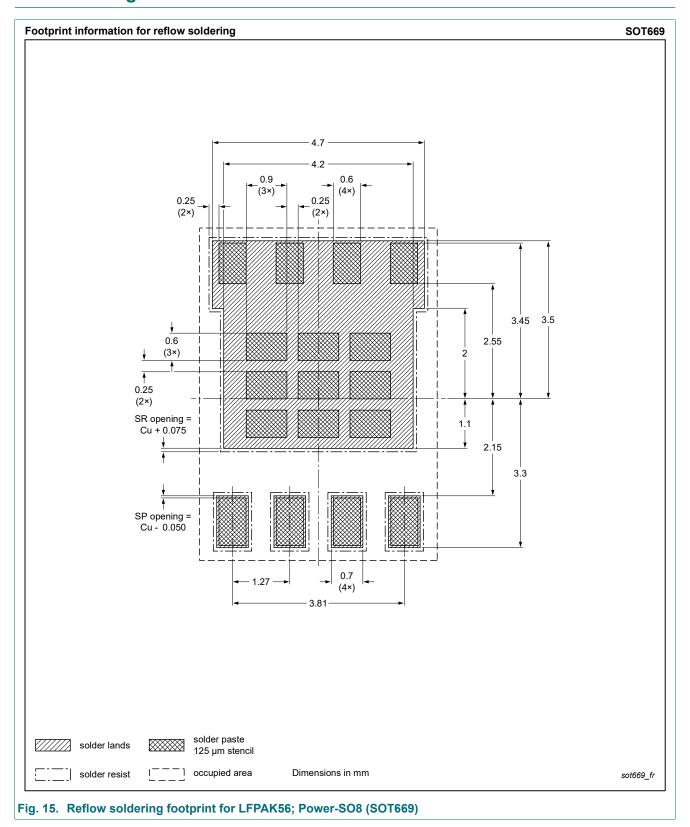


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

60 V, 10 A PNP high power bipolar transistor

# 13. Soldering



60 V, 10 A PNP high power bipolar transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PHPT60610PY v.2	20190115	Product data sheet	-	PHPT60610PY v.1				
Modifications:	Typo at figures 2 and 3: unit corrected from ns to s at x-scale							
PHPT60610PY v.1	20150527	Product data sheet	-	-				

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

#### **Definitions**

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### **Disclaimers**

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Nexperia takes no responsibility for the content in this document if provided by an information source outside of Nexperia.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the Terms and conditions of commercial sale of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use in automotive applications** — This Nexperia product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or

#### 60 V, 10 A PNP high power bipolar transistor

equipment, nor in applications where failure or malfunction of an Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia and its suppliers accept no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nexperia.com/profile/terms">http://www.nexperia.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### **Trademarks**

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### 60 V, 10 A PNP high power bipolar transistor

### **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10	. Characteristics	5
11.	. Test information	8
12	. Package outline	g
	Soldering	
	Revision history	
	Legal information	

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 15 January 2019

<sup>©</sup> Nexperia B.V. 2019. All rights reserved

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by NXP manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G

NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 NTE65 C4460 SBC846BLT3G 2SA1419T
TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176

FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E

CMXT2207 TR CPH6501-TL-E MCH4021-TL-E TTC012(Q) BULD128DT4 DDTC114EUAQ-7-F NJL0281DG NSS20500UW3TBG

732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H SZT1010T1G 873787E